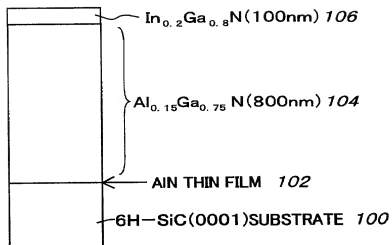
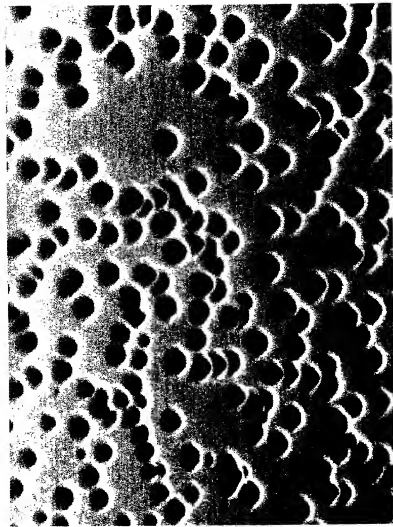


FIG. 1



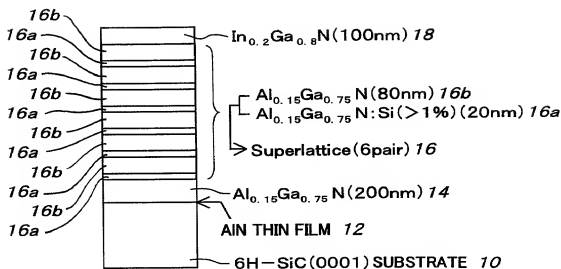
TOTERO-222E4660

FIG. 2



0.5 μm

FIG. 3



094322.087101

101E80'222E+660

FIG. 4

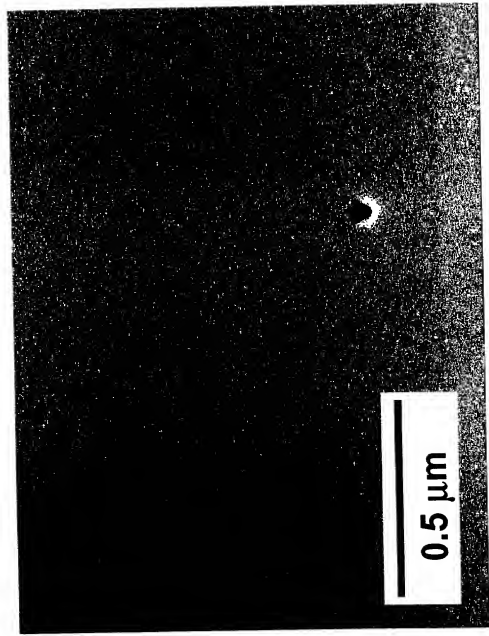


FIG. 6

TIMING CHART FOR INTRODUCING MATERIAL GASES

00943262-000101

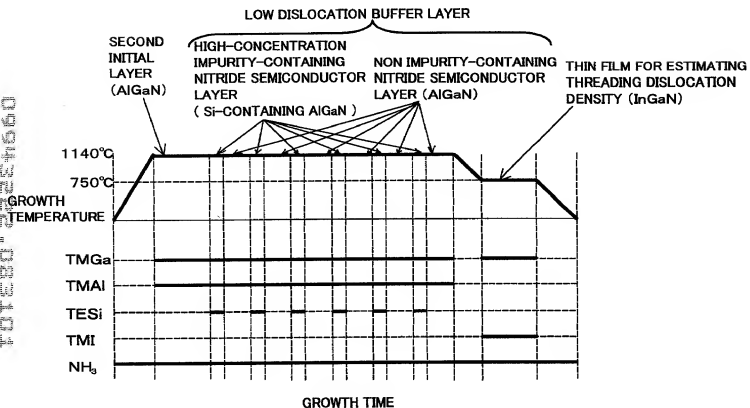


FIG. 7

RELATIONSHIP BETWEEN TESi FLOW RATE
AND THREADING DISLOCATION DENSITY

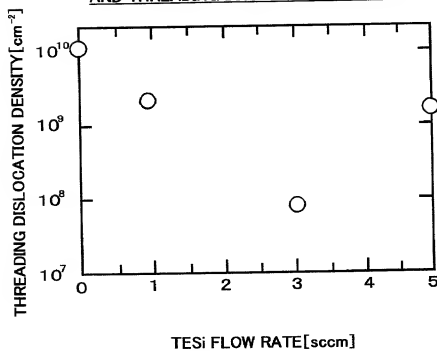
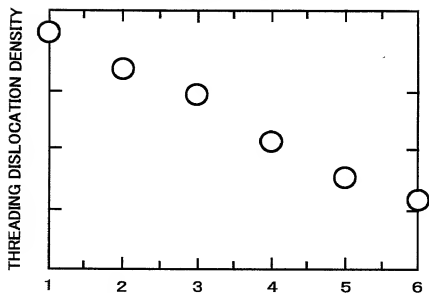


FIG. 8

RELATIONSHIP BETWEEN PERIOD OF
SUPERLATTICE BUFFER LAYER AND
THREADING DISLOCATION DENSITY



PERIODICITY OF SUPERLATTICE BUFFER LAYER (NUMBER OF TIMES)

00943222.00304
TOTAL: 222460

FIG. 9

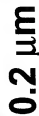
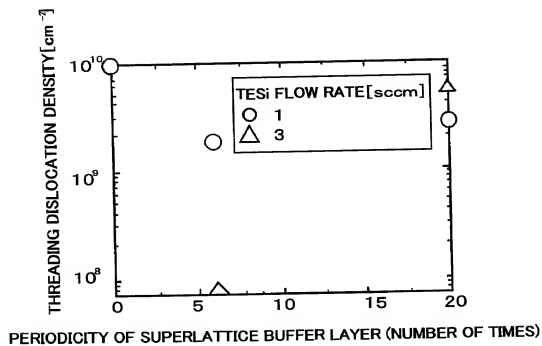


FIG. 10



[illegible]

SiC SUBSTRATE 10

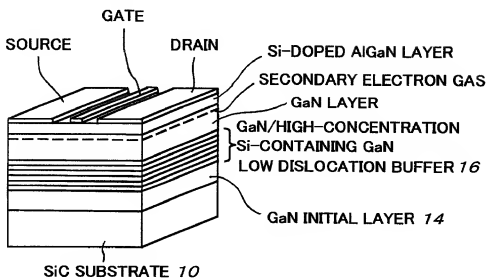
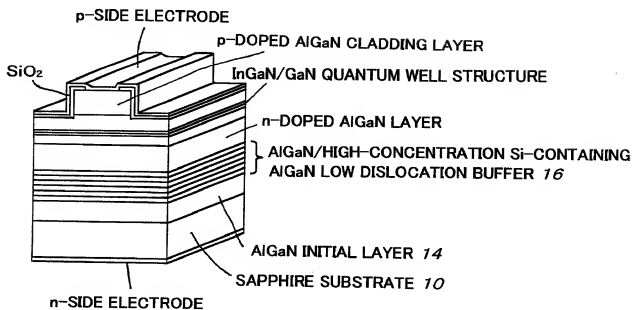


FIG. 12

NITRIDE SEMICONDUCTOR LASER DIODE
(EXAMPLE, InGaN LASER)



094322.08301